

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Ryu et al. Serial No.: 09/911,995 Filed: July 24, 2001

Group Art Unit: 2811 Confirmation No.: 5240 Examiner: Gene Munson

For: SI

SILICON CARBIDE POWER METAL-OXIDE SEMICONDUCTOR FIELD EFFECT TRANSISTORS HAVING A SHORTING CHANNEL AND METHODS OF FABRICATING SILICON CARBIDE METAL-OXIDE SEMICONDUCTOR

FIELD EFFECT TRANSISTORS HAVING A SHORTING CHANNEL

July 3, 2003

Mail Stop RCE Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

Attached is a form PTO-1449, together with a copy of the identified document(s). This Information Disclosure Statement is submitted in accordance with 37 C.F.R. \$1.97(b), before mailing of a first Office Action in the Request for Continued Examination is above-referenced application filed concurrently herewith. It is requested that these documents be considered by the Examiner and officially made of record in accordance with the provisions of 37 C.F.R. § 1.97 and Section 609 of the MPEP.

In particular, copies of documents 5 and 6 on the attached Form PTO-1449 have been previously provided to the Patent Office with previously submitted IDSs but not considered by the Examiner. It is requested that these documents be considered by the Examiner and officially made of record in accordance with the provisions of 37 C.F.R. § 1.97 and Section 609 of the M.P.E.P, as Applicants have complied with the requirements of this section.

Applicants note that the Examiner struck through documents 5-6 listed on the attached PTO-1449 form and indicated that no publication data was available. Applicants submit the present IDS with an RCE responsive to a telephonic request from Examiner Munson and, request that the Examiner consider these references as prior art under 35 U.S.C. § 102(f) for purposes of examination of the present application. Applicants have included a publication corresponding to item 5 on the form PTO-1449 along with item 5 as requested by Examiner Munson. Applicants respectfully request that Examiner Munson consider the references at this time. Applicants appreciate Examiner Munson's assistance with this matter.

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No fee is believed due. However, the Commissioner is hereby authorized to charge any deficiency or credit any overpayment to our Deposit Account No. 50-0220.

Respectfully submitted,

Elizabeth A. Stanek

Registration No. 48,568



PATENT TRADEMARK OFFICE

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Date of Deposit: July 3, 2003

I hereby certify that this paper or fee is being deposited with the United States Postal Service "Express Mail Post Office to Addressee" service under 37 CFR 1.10 on the date indicated above and is addressed to Mail Stop RCE, Commissioner of Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Susan E. Freedman

Date of Signature: July 3, 2003

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C	omplete if Known
Application Number	09/911,995
Filing Date	07/24/2001
First Named Inventor	Sei-Hyung Rhu
Group Art Unit	2811
Examiner Name	Gene Munson
Attorney Docket Number	5308-156

		 	U.S. PATE	NTS AND PATENT PUBLICATION	ONS	
Examiner Cite N	Cite No.	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document	Pages, Columns, Lines, Where Relevant Passages
		Number	Kind Code (if known)	of Gled Document	MM-DD-YYYY	or Relevant Figures Appear
	1	6,136,728		Wang	10/24/2000	
	2	6,063,698		Tseng et al.	05/16/2000	
	3	6,048,766		Gardner et al.	04/11/2000	
	4	6,028,012		Wang	02/22/2000	
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		OTHER NON PATENT LITERATURE DOCUMENTS
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published
	5	G.Y. Chung, C.C. Tin, J.R. Williams, K. McDonald, R.A. Weller, S.T. Pantelides, L.C. Feldmar, M.K. Das, and J.W. Palmour, "Improved Inversion Channel Mobility for 4H-SiC MOSETs Following High Temperature Anneals in Nitric Oxide," <i>IEEE Electron Device Letters</i> accepted for publication 2000 and published in Vol. 22, No. 4, April 2001
	6	Das, Mrinal K. Graduate thesis entitled, Fundamental Studies of the Silicon Carbide MOS Structure. Purdue University, December 1999

Examiner Signature	Date Considered	